NCE N-Channel Super Trench Power MOSFET

Description

The NCEP60T12AK uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

V_{DS} =60V,I_D =120A

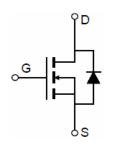
 $R_{DS(ON)} < 4.0 \text{m}\Omega$ @ $V_{GS} = 10 \text{V}$ (Typ:3.5m Ω) $R_{DS(ON)} < 5.0 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$ (Typ:4.0m Ω)

- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

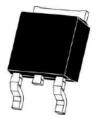
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!
100% ΔVds TESTED!





Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP60T12AK	NCEP60T12AK	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous (Silicon Limited)	I _D	120	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	100	Α
Pulsed Drain Current	I _{DM}	480	Α
Maximum Power Dissipation	P _D	180	W
Derating factor		1.2	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	500	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$



NCEP60T12AK

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{eJC}	0.83	°C/W	Ī
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.7	2.4	V
Drain-Source On-State Resistance	-	V _{GS} =10V, I _D =60A -		3.5	4.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =60A	-	4.0	5.0	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =60A	40	-	-	S
Dynamic Characteristics (Note4)		0,				
Input Capacitance	C _{lss}	V _{DS} =30V,V _{GS} =0V,	-	4000	-	PF
Output Capacitance	Coss	$V_{DS}=30V,V_{GS}=0V,$ $F=1.0MHz$	_	680	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1:uivinz	_	23	-	PF
Switching Characteristics (Note 4)		0,0				
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	tr	V_{DD} =30 V , I_{D} =60 A	_	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10 V , R_{G} =4.7 Ω	-	56	-	nS
Turn-Off Fall Time	t _f		_	12	-	nS
Total Gate Charge	Q_g	V -20VI -C0A	-	67		nC
Gate-Source Charge	Q _{gs}	V_{DS} =30V, I_D =60A, V_{GS} =10V	_	12		nC
Gate-Drain Charge	Q_{gd}	V _{GS} -10V	_	8.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =120A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	120	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = I_S$	-	48		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	60		nC

Notes:

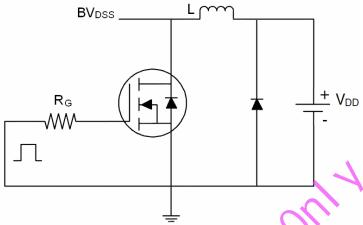
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=30V,V_G=10V,L=0.5mH,Rg=25 Ω



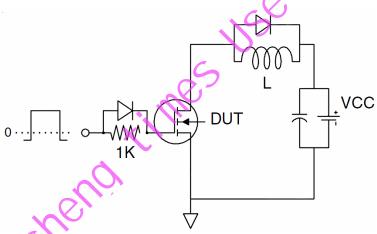


Test Circuit

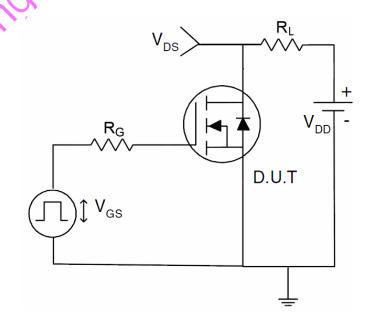
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





NCEP60T12AK

Typical Electrical and Thermal Characteristics

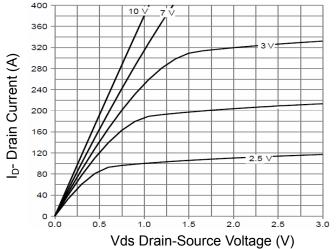


Figure 1 Output Characteristics

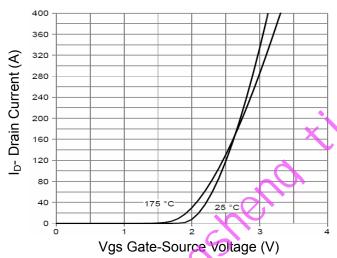


Figure 2 Transfer Characteristics

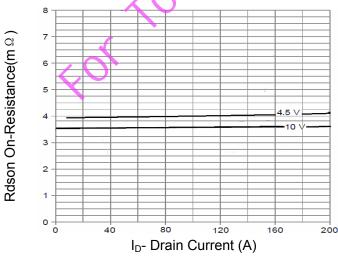


Figure 3 Rdson- Drain Current

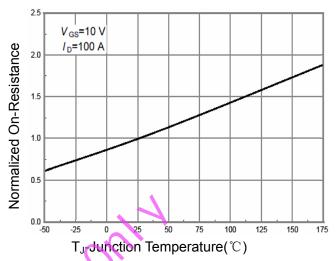


Figure 4 Rdson-JunctionTemperature

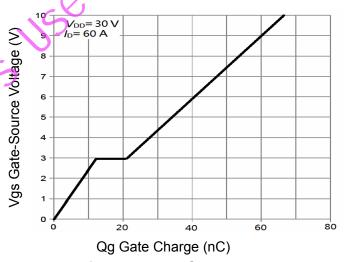


Figure 5 Gate Charge

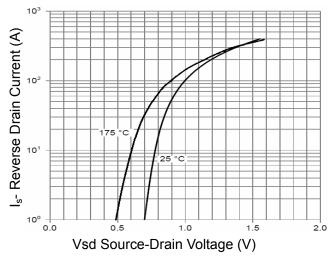
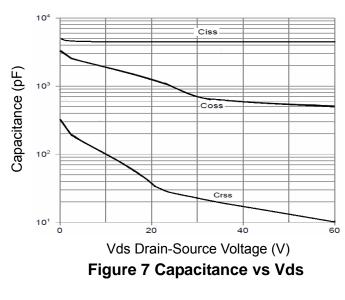


Figure 6 Source- Drain Diode Forward

NCEP60T12AK



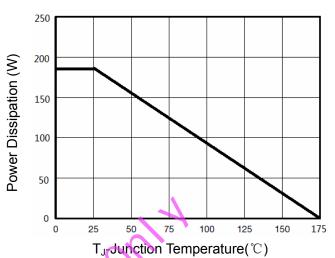
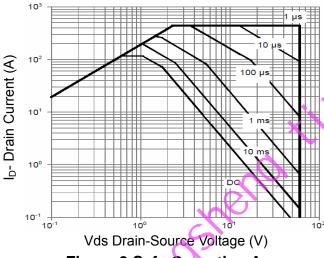


Figure 9 Power De-rating



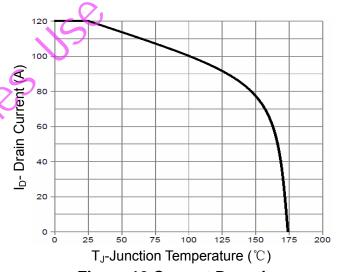


Figure 8 Safe Operation Area

Figure 10 Current De-rating



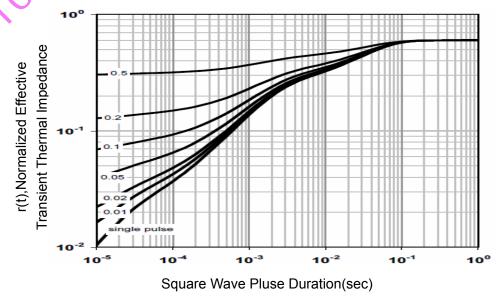
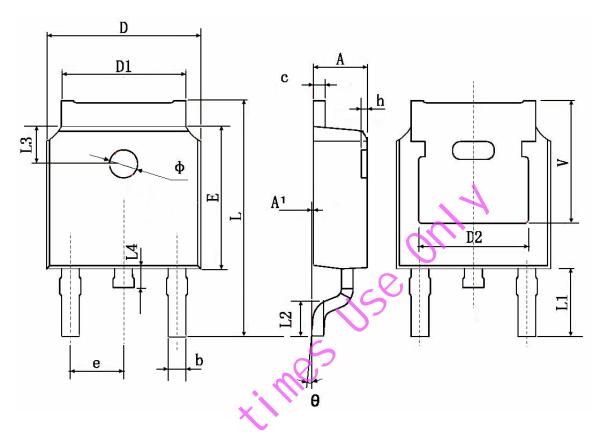


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D 🔏	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2 (4.830 TYP.		0.190 TYP.		
√ €)	6.000	6.200	0.236	0.244	
e	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114	TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	5.350 TYP.		TYP.	



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